

# HETERO-INTERFACES FOR EXTREME ELECTRONIC ENVIRONMENTS

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- Quasi-two-dimensional electron gas in oxide based hetero-interfaces:
  - Recently discovered (2004) → Tunability (2006)
- Investigated for nano-device applications (i.e, non-volatile memory)
- Extreme environment applications are possible
  - Incorporation of ultra-thin high-K dielectric (dielectric constant,  $K=25$ ) film that eliminates the need for a gate dielectric.
  - Insulating film and the substrate increases radiation hardening
- The science behind Q-2D-EG and its tunability is still not clear.
  - 1- Polar catastrophe at the polar LAO/non-polar STO interface, 2- structural distortions at the interface, 3- oxygen vacancies introduced into the LAO/STO hetero-structure during the growth of LAO, 4- preferential cationic intermixing at the interface.
- A large number of parameters can effect both the existence and the magnitude of the interface conductivity.
  - Substrate quality
  - Film composition
  - Defects
  - Strain development
  - Film thickness
  - Electrode materials
  - Film surface conditions
  - In plane anisotropy.

All have different dependence on temperature.  
Therefore any extreme environment application  
requires quantitative analysis of these parameters.

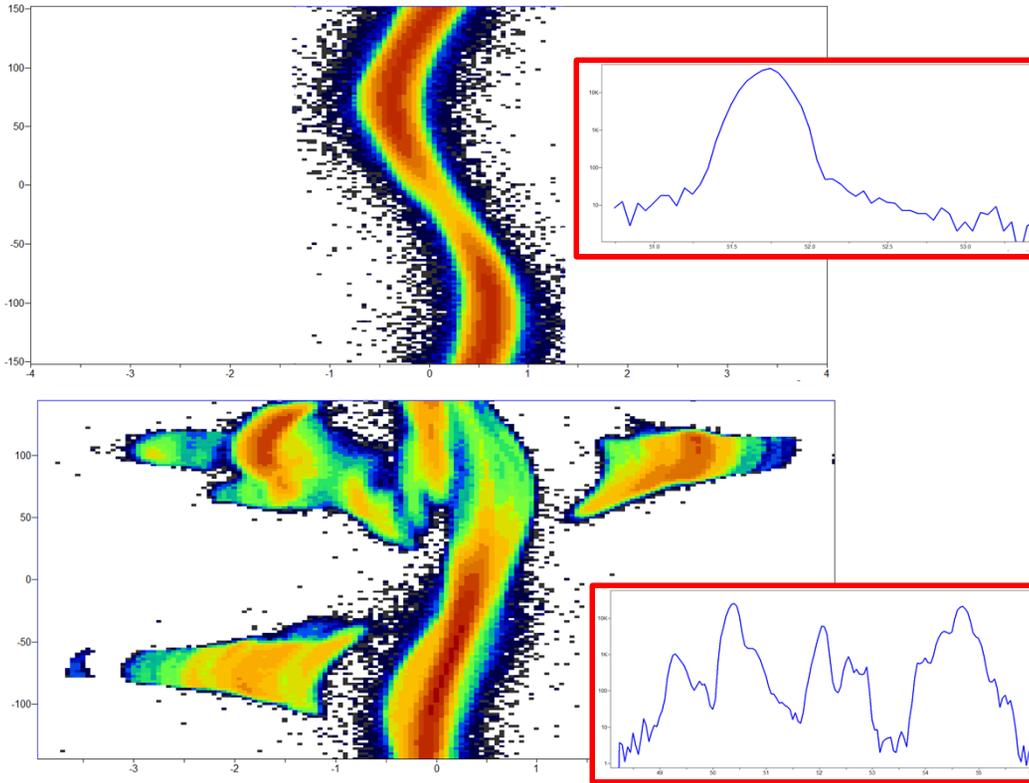
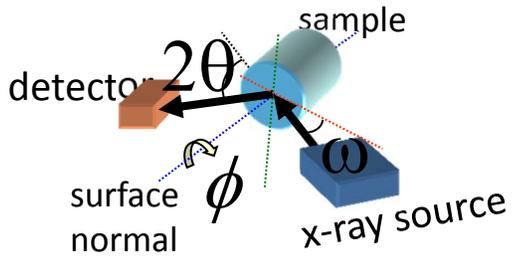
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Form Approved  
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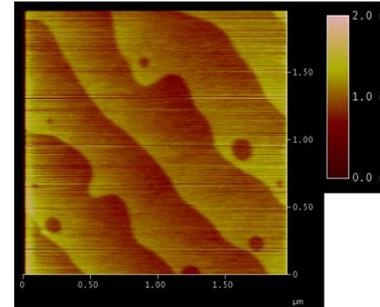
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1. REPORT DATE <b>SEP 2012</b>		2. REPORT TYPE		3. DATES COVERED <b>00-00-2012 to 00-00-2012</b>	
4. TITLE AND SUBTITLE <b>Hetero-Interfaces for Extreme Electronic Environments</b>				5a. CONTRACT NUMBER	
				5b. GRANT NUMBER	
				5c. PROGRAM ELEMENT NUMBER	
6. AUTHOR(S)				5d. PROJECT NUMBER	
				5e. TASK NUMBER	
				5f. WORK UNIT NUMBER	
7. PERFORMING ORGANIZATION NAME(S) AND ADDRESS(ES) <b>Case Western Reserve University, Department of Materials Science &amp; Engineering, White Building, 10900 Euclid Ave, Cleveland, OH, 44106-7204</b>				8. PERFORMING ORGANIZATION REPORT NUMBER	
9. SPONSORING/MONITORING AGENCY NAME(S) AND ADDRESS(ES)				10. SPONSOR/MONITOR'S ACRONYM(S)	
				11. SPONSOR/MONITOR'S REPORT NUMBER(S)	
12. DISTRIBUTION/AVAILABILITY STATEMENT <b>Approved for public release; distribution unlimited</b>					
13. SUPPLEMENTARY NOTES <b>Presented at the 2012 AFOSR Space Propulsion and Power Program Review held 10-13 September in Arlington, VA. U.S. Government or Federal Rights License</b>					
14. ABSTRACT					
15. SUBJECT TERMS					
16. SECURITY CLASSIFICATION OF:			17. LIMITATION OF ABSTRACT <b>Same as Report (SAR)</b>	18. NUMBER OF PAGES <b>4</b>	19a. NAME OF RESPONSIBLE PERSON
a. REPORT <b>unclassified</b>	b. ABSTRACT <b>unclassified</b>	c. THIS PAGE <b>unclassified</b>			

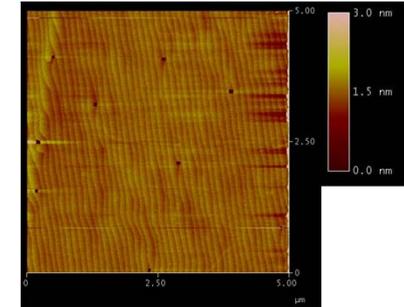
# Substrates



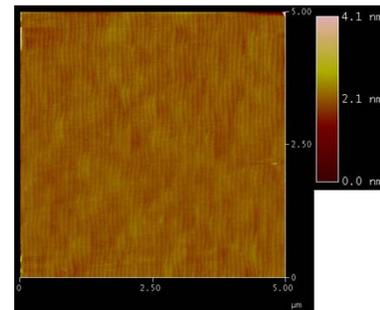
Commercial finishing  
with etch pits



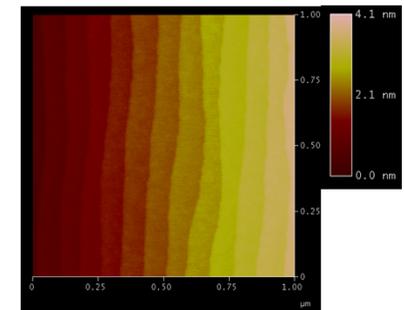
Our finishing  
with etch pits at pH = 5.7



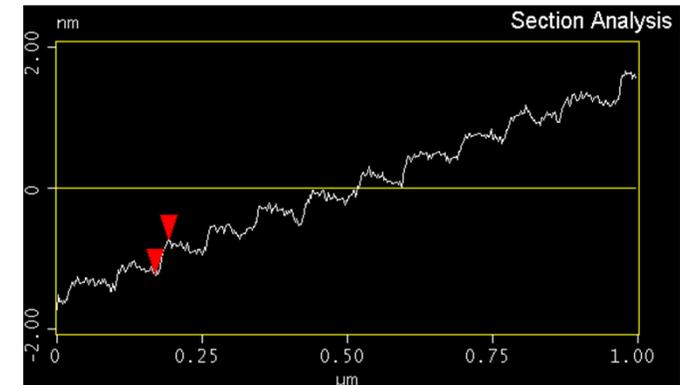
Etch pit free  
surfaces at pH = 5.7



Profile showing  
the flat terraces



4Å steps = unit cell size (Ti-terminated)



- Substrate quality depends on the company
- The curvature is due to the mis-cut angle  
Larger the mis-cut angle, narrower the terraces (AFM)
- $\sim 4\text{\AA}$  steps = unit cell size (Ti-terminated)
- Commercially prepared surfaces show etching pits.
- We showed that at pH=6 we can get etch pit free surfaces

# Reciprocal space mapping

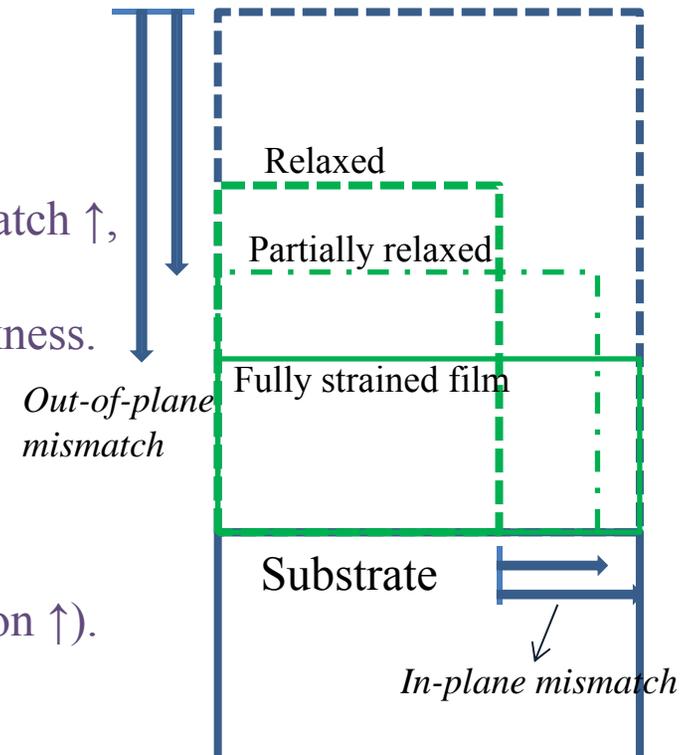
Bulk LAO: 0.3791 nm Bulk STO: 0.3905 nm

In-plane direction:

- LaAlO<sub>3</sub> films are under tensile strain.
- As thickness increases: Stress ↑, Lattice constant ↓, Mismatch ↑, Strain ↓
- Partial relaxation in LaAlO<sub>3</sub> films with increasing film thickness.
- Above 80nm film thickness: Plastic deformation due to large strain. Residual film remains highly strained.

Out-of-plane direction:

- LaAlO<sub>3</sub> films are tetragonally distorted.
- Degree of tetragonality is decreased as thickness ↑ (relaxation ↑).
- Residual film above 80nm is still tetragonally distorted.

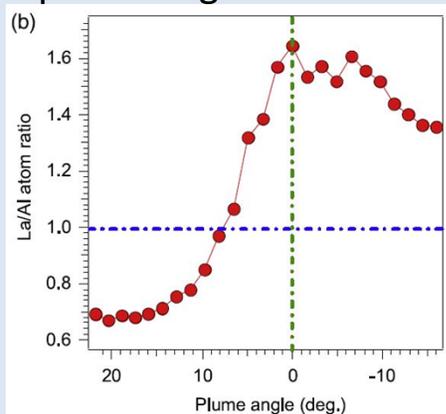


Wei Wei and Alp Sehirlioglu, Appl. Phys. Lett., **100**, 071901 (2012)

Laser pulse	Thickness (nm)	$f_{pp}$	$f_{pl}$	$\epsilon_{pp}$	$\epsilon_{pl}$	$a_{pp}$ (nm)	$a_{pl}$ (nm)	Relaxation rate	$a_{pp}/a_{pl}$
100	4.9	- 0.03958		- 0.00913		0.375045			
200	7.9	- 0.03522	- 0.00056	- 0.00437	0.03139	0.376750	0.390280	1.83%	0.965332
500	18.3	- 0.03358	- 0.00076	- 0.00268	0.03119	0.377390	0.390202	2.48%	0.967165
1000	38.4	- 0.03326	- 0.00100	- 0.00261	0.03067	0.377513	0.390109	3.26%	0.967711
1500	65.4	- 0.02987	- 0.00117	- 0.00321	0.03050	0.377284	0.390041	3.83%	0.967293
2000	84	- 0.03322	- 0.00052	- 0.00257	0.03117	0.377529	0.390298	1.68%	0.967283

# Composition

La/Al ratio in the film and the level of intermixing can depend on plume angle

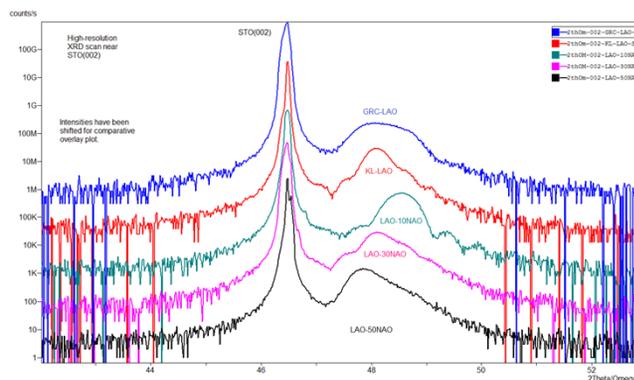
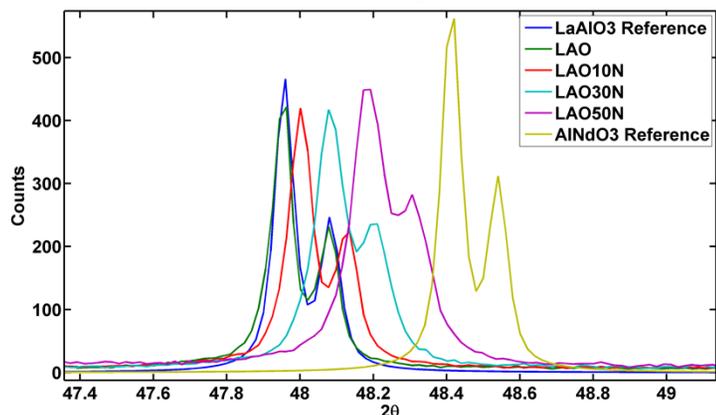
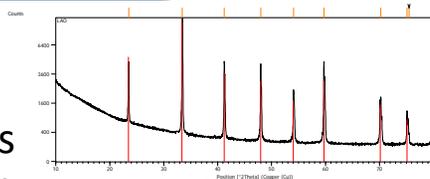


T.C. Droubay, et al. Appl. Phys. Lett. **97**, 124105 (2010).

- The composition of target and the film can be different when multiple single-site cations exist.
- The composition of the film can be different for targets of same composition but different source.

Sample	O	La	Nd	Al	(La + Nd)/Al	Nd/La
LAO-CWRU	66.13	20.25	0	13.62	1.48	0
LAO-Kurt Lesker	62.85	25.93	0	11.22	2.31	0
LAO-10NAO	67.03	18.88	0.69	13.39	1.46	0.036
LAO-30NAO	67.38	18.13	5.14	9.35	2.48	0.28
LAO-50NAO	65.93	15.54	8.97	9.56	2.56	0.57

Single phase targets with controlled lattice parameters



Film lattice parameters and composition do not follow that of target.